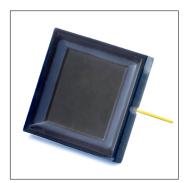


# Photodiode 100 mm<sup>2</sup> with Integrated Thin Film Filter



### FEATURES

- 100 mm<sup>2</sup> Square Active Area
- Responsivity @ 3 nm 0.16 A/W
- Detection Range 1 nm to 12 nm
- Shipped with Protective Cover

### **Electro-Optical Characteristics at 25°C**

Parameters	Test Conditions	Min	Тур	Max	Units
Active Area	10 mm x 10 mm		100		mm <sup>2</sup>
Responsivity	(see graph on next page)		0.16		A/W
Shunt Resistance, Rsh	@ ±10 mV	20			Ohms
Reverse Breakdown Voltage, $V_R$	1 <sub>R</sub> = 1 μA	5	10		Volts
Capacitance, C	V <sub>R</sub> = 0 V		10	44	nF

#### **Thermal Parameters**

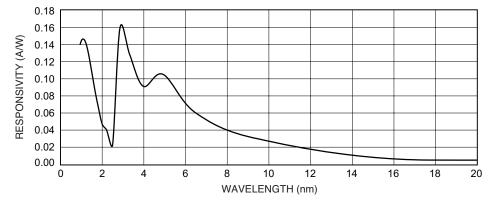
Storage and Operating Temperature Range	Units		
Ambient	-10° to 40°C		
Nitrogen or Vacuum	–20 to 80°C		
Lead Soldering Temperature*	260°C		

\*0.080" from case for 10 seconds.

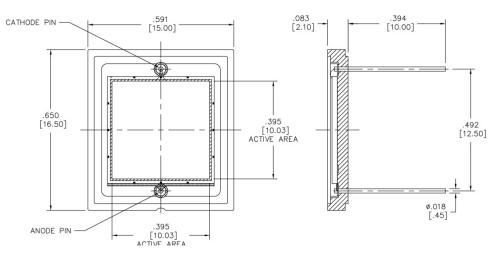


## Photodiode 100 mm<sup>2</sup> with Integrated Thin Film Filter

**Typical Responsivity at 25°C** 



#### **Package Information**



Dimensions are in inch [metric] units.

Specifications are subject to change without prior notice.